

# Victor Vainberg

## List of Publications by Year in descending order

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28  
papers

76  
citations

1684188

5  
h-index

1588992

8  
g-index

29  
all docs

29  
docs citations

29  
times ranked

38  
citing authors

#	ARTICLE	IF	CITATIONS
1	Electron mobility in the GaAs/InGaAs/GaAs quantum wells. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2013, 16, 152-161.	1.0	14
2	Lateral transport and far-infrared radiation of electrons in In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs heterostructures with the double tunnel-coupled quantum wells in a high electric field. Semiconductors, 2010, 44, 1495-1498.	0.5	9
3	Transport properties of InGaAs/GaAs Heterostructures with $\delta$ -doped quantum wells. Semiconductors, 2012, 46, 631-636.	0.5	9
4	Magnetoresistance of TVO temperature sensor at T<1â€K. Review of Scientific Instruments, 2009, 80, 094902.	1.3	7
5	Influence of conduction via a channel of an impurity $\delta$ -layer on the magneto-quantum effects in AlGaAs/GaAs/AlGaAs heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 60, 31-36.	2.7	5
6	Thermometric characteristics of carbon fibres. Sensors and Actuators A: Physical, 1993, 39, 237-240.	4.1	4
7	Low-temperature sensors based on telluride microcrystals. Sensors and Actuators A: Physical, 1992, 30, 55-58.	4.1	3
8	Long-term photoconductivity decay in n-InGaAs/GaAs heterostructures with coupled quantum wells under band-to-band excitation. Semiconductors, 2013, 47, 174-177.	0.5	3
9	A peculiarity of quantum hot-electron real space transfer in dual-channel GaAs-based heterostructures. Journal of Physics Communications, 2017, 1, 045002.	1.2	3
10	Effect of barrier width between GaAs/InGaAs/GaAs double coupled quantum wells on bipolar transport and terahertz radiation by hot carriers in lateral electric field. Low Temperature Physics, 2020, 46, 633-638.	0.6	3
11	Negative contrast IR emitting device based on the carrier contact exclusion. Semiconductor Science and Technology, 2003, 18, 697-702.	2.0	2
12	Magnetoresistance of composite carbon sensors in strong electric fields in the liquid helium temperature range. Low Temperature Physics, 2017, 43, 367-370.	0.6	2
13	Electric transport properties in the 2D-MoS <sub>2</sub> . Molecular Crystals and Liquid Crystals, 2022, 749, 87-92.	0.9	2
14	Charge-carrier exclusion and accumulation intensified by ohmic contacts. Semiconductors, 1998, 32, 568-571.	0.5	1
15	The transient exclusion effect in intrinsic semiconductors. Semiconductor Science and Technology, 2002, 17, 1058-1063.	2.0	1
16	Energy characteristics of boron impurity in Si $\delta$ -Si $\delta$ -xGex heterostructures with on-center and on-edge selective doping of quantum wells. Low Temperature Physics, 2007, 33, 869-871.	0.6	1
17	Influence of narrow inner barriers on the low-temperature lateral conduction in quantum wells. Low Temperature Physics, 2014, 40, 531-536.	0.6	1
18	The effect of structure on the low-temperature electrical conductivity of carbon nanocomposite temperature sensors. Low Temperature Physics, 2019, 45, 1104-1108.	0.6	1

#	ARTICLE	IF	CITATIONS
19	Long-term stability of TVO low-temperature sensors before and after gamma irradiation with a high dose. <i>Low Temperature Physics</i> , 2021, 47, 306-311.	0.6	1
20	Effects of the Real-Space Transfer of Charge Carriers in the n-AlGaAs/GaAs Heterostructures with the Delta-Layers of Impurity in the Barriers. <i>Ukrainian Journal of Physics</i> , 2014, 59, 721-725.	0.2	1
21	Low temperature charge transport in arrays of single-walled carbon nanotube bundles with radiation induced defects. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2019, 22, 418-423.	1.0	1
22	Resistive switching effect in the <i>n</i> -InGaAs/GaAs heterostructures with double tunnel-coupled quantum wells. <i>Low Temperature Physics</i> , 2022, 48, 157-160.	0.6	1
23	Transient processes in electric transport in the powder MoS <sub>2</sub> samples. <i>Journal of Applied Physics</i> , 2022, 131, .	2.5	1
24	Exclusion in the semiconductor p+p-p+structure under conditions of a temperature gradient. <i>Semiconductor Science and Technology</i> , 1998, 13, 54-58.	2.0	0
25	IR study of exclusion-accumulation effects enhanced by the geometrical factor. <i>Semiconductor Science and Technology</i> , 2000, 15, 1054-1060.	2.0	0
26	UP-conversion of terahertz radiation induced by photon drag effect. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 20, 563-566.	2.7	0
27	Negative residual infrared photoconduction in the p-SiGe/Si heterostructures with selectively doped quantum wells. <i>Journal of Applied Physics</i> , 2012, 112, 083715.	2.5	0
28	Application of Semiconductor Whisker Crystals in Low Temperature Electronics. <i>European Physical Journal Special Topics</i> , 1996, 06, C3-429-C3-434.	0.2	0